

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Atty. Docket

DOEDE TERPSTRA ET AL

NL 000383

Serial No.

Group Art Unit

Filed: CONCURRENTLY

Ex.

Title: METHOD OF MANUFACTURING A BIPOLAR TRANSISTOR SEMICONDUCTOR
DEVICE

Commissioner for Patents
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to calculation of the filing fee and examination, please
amend the above-identified application as follows:

IN THE CLAIMS

Please amend the claims as follows:

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3. (amended) A method as claimed in claim 1, characterized in
that after the formation of the intrinsic base region, a layer of
an electrically insulating material is provided, which is subjected
to an etching operation so as to form spacers on edges of the base
contact and the collector contact, causing these contacts to be